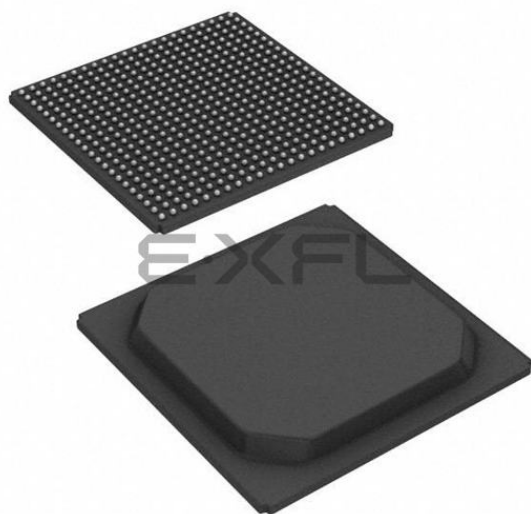




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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

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Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	300000
Total RAM Bits	21094400
Number of I/O	244
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	484-BBGA, FCBGA
Supplier Device Package	484-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf300tl-fcg484e

4 Device Offering

The following table lists the PolarFire FPGA device options using the MPF300T as an example. The MPF100T, MPF200T, and MPF500T device densities have identical offerings.

Table 1 • PolarFire FPGA Device Options

Device Options	Extended Commercial 0 °C–100 °C	Industrial –40 °C–100 °C	STD	–1	Transceivers T	Lower Static Power L	Data Security S
MPF300T	Yes	Yes	Yes	Yes	Yes		
MPF300TL	Yes	Yes	Yes		Yes	Yes	
MPF300TS		Yes	Yes	Yes	Yes		Yes
MPF300TLS		Yes	Yes		Yes	Yes	Yes

6 DC Characteristics

This section lists the DC characteristics of the PolarFire FPGA device.

6.1 Absolute Maximum Rating

The following table lists the absolute maximum ratings for PolarFire devices.

Table 3 • Absolute Maximum Rating

Parameter	Symbol	Min	Max	Unit
FPGA core power supply	V _{DD}	−0.5	1.13	V
Transceiver Tx and Rx lanes supply	V _{DDA}	−0.5	1.13	V
Programming and HSIO receiver supply	V _{DD18}	−0.5	2.0	V
FPGA core and FPGA PLL high-voltage supply	V _{DD25}	−0.5	2.7	V
Transceiver PLL high-voltage supply	V _{DDA25}	−0.5	2.7	V
Transceiver reference clock supply	V _{DD_XCVR_CLK}	−0.5	3.6	V
Global V _{REF} for transceiver reference clocks	XCVR _{VREF}	−0.5	3.6	V
HSIO DC I/O supply ²	V _{DDIx}	−0.5	2.0	V
GPIO DC I/O supply ²	V _{DDIx}	−0.5	3.6	V
Dedicated I/O DC supply for JTAG and SPI	V _{DDI3}	−0.5	3.6	V
GPIO auxiliary power supply for I/O bank x ²	V _{DDAUXx}	−0.5	3.6	V
Maximum DC input voltage on GPIO	V _{IN}	−0.5	3.8	V
Maximum DC input voltage on HSIO	V _{IN}	−0.5	2.2	V
Transceiver Receiver absolute input voltage	Transceiver V _{IN}	−0.5	1.26	V
Transceiver Reference clock absolute input voltage	Transceiver REFCLK V _{IN}	−0.5	3.6	V
Storage temperature (ambient) ¹	T _{STG}	−65	150	°C
Junction temperature ¹	T _J	−55	135	°C
Maximum soldering temperature RoHS	T _{SOLROHS}		260	°C
Maximum soldering temperature leaded	T _{SOLPB}		220	°C

1. See [FPGA Programming Cycles vs Retention Characteristics](#) for retention time vs. temperature. The total time used in calculating the device retention includes storage time and the device stored temperature.
2. The power supplies for a given I/O bank x are shown as V_{DDIx} and V_{DDAUXx}.

6.2 Recommended Operating Conditions

The following table lists the recommended operating conditions.

Table 4 • Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
FPGA core supply at 1.0 V mode ¹	V _{DD}	0.97	1.00	1.03	V
FPGA core supply at 1.05 V mode ¹	V _{DD}	1.02	1.05	1.08	V
Transceiver TX and RX lanes supply at 1.0 V mode (when all lane rates are 10.3125 Gbps or less) ¹	V _{DDA}	0.97	1.00	1.03	V

Table 8 • Maximum Overshoot During Transitions for GPIO

AC (V _{IN}) Overshoot Duration as % at T _J = 100 °C	Condition (V)
100	3.8
100	3.85
100	3.9
100	3.95
70	4
50	4.05
33	4.1
22	4.15
14	4.2
9.8	4.25
6.5	4.3
4.4	4.35
3	4.4
2	4.45
1.4	4.5
0.9	4.55
0.6	4.6

Note: Overshoot level is for V_{DDI} at 3.3 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for GPIO.

Table 9 • Maximum Undershoot During Transitions for GPIO

AC (V _{IN}) Undershoot Duration as % at T _J = 100 °C	Condition (V)
100	-0.5
100	-0.55
100	-0.6
100	-0.65
100	-0.7
100	-0.75
100	-0.8
100	-0.85
100	-0.9
100	-0.95
100	-1
100	-1.05
100	-1.1
100	-1.15
100	-1.2
69	-1.25
45	-1.3

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
HSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSTL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL12II ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL18I ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /55	(V _{DDI} – V _{OH}) /55
HSUL18II ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH}) /40
POD12I ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /48	(V _{DDI} – V _{OH}) /48
POD12II ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /34	(V _{DDI} – V _{OH}) /34

1. Drive strengths per PCI specification V/I curves.
2. Refer to [UG0686: PolarFire FPGA User I/O User Guide](#) for details on supported drive strengths.
3. For external stub-series resistance. This resistance is on-die for GPIO.
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).
5. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
6. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

6.3.2 Differential DC Input and Output Levels

The follow tables list the differential DC I/O levels.

Table 14 • Differential DC Input Levels

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V _{ICM} ^{1,3} Min (V)	V _{ICM} ^{1,3} Typ (V)	V _{ICM} ^{1,3} Max (V)	V _{ID} ² Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
LVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS18 ⁴	GPIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6

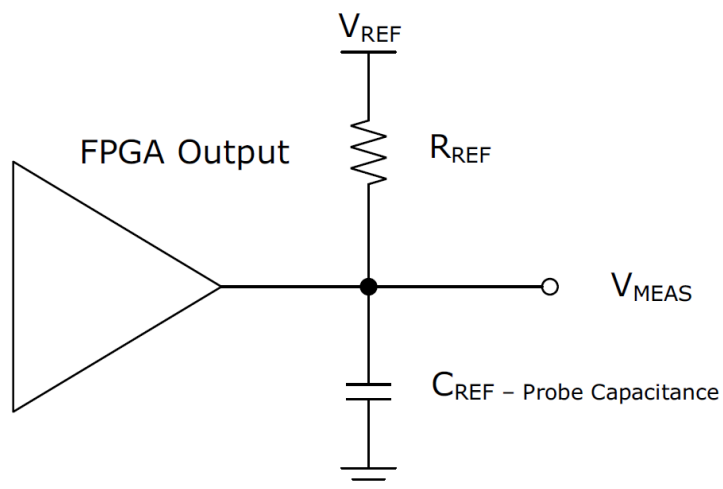
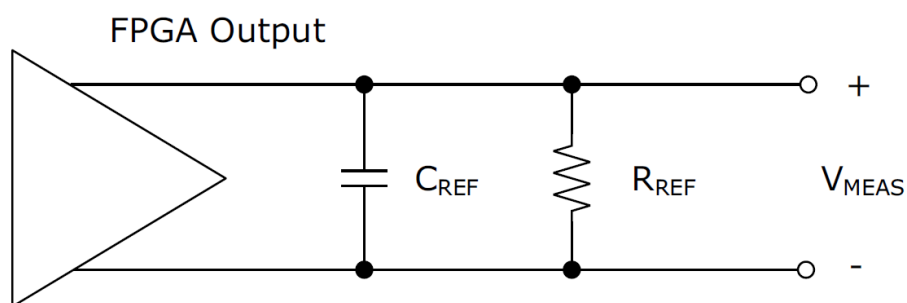
I/O Standard	Bank Type	VICM_RANGE Libero Setting	V _{ICM1,3} Min (V)	V _{ICM1,3} Typ (V)	V _{ICM1,3} Max (V)	V _{ID} ² Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
LVDS18	HSIO	Low	0.05	0.4	0.8	0.1	0.35	0.6
		Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LCMDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LCMDS18	HSIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LCMDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
RSDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.2	0.6
		Low	0.05	0.4	0.8	0.1	0.2	0.6
RSDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.2	0.6
		Low	0.05	0.4	0.8	0.1	0.2	0.6
RSDS18 ⁵	HSIO	Mid (default)	0.6	1.25	1.65	0.1	0.2	0.6
		Low	0.05	0.4	0.8	0.1	0.2	0.6
MINILVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.3	0.6
		Low	0.05	0.4	0.8	0.1	0.3	0.6
MINILVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.3	0.6
		Low	0.05	0.4	0.8	0.1	0.3	0.6
MINILVDS18 ⁵	HSIO	Mid (default)	0.6	1.25	1.65	0.1	0.3	0.6
		Low	0.05	0.4	0.8	0.1	0.3	0.6
SUBLVDS33	GPIO	Mid (default)	0.6	0.9	2.35	0.1	0.15	0.3
		Low	0.05	0.4	0.8	0.1	0.15	0.3
SUBLVDS25	GPIO	Mid (default)	0.6	0.9	2.35	0.1	0.15	0.3
		Low	0.05	0.4	0.8	0.1	0.15	0.3
SUBLVDS18 ⁵	HSIO	Mid (default)	0.6	0.9	1.65	0.1	0.15	0.3
		Low	0.05	0.4	0.8	0.1	0.15	0.3
PPDS33	GPIO	Mid (default)	0.6	0.8	2.35	0.1	0.2	0.6
		Low	0.05	0.4	0.8	0.1	0.2	0.6
PPDS25	GPIO	Mid (default)	0.6	0.8	2.35	0.1	0.2	0.6
		Low	0.05	0.4	0.8	0.1	0.2	0.6
PPDS18 ⁵	HSIO	Mid (default)	0.6	0.8	1.65	0.1	0.2	0.6
		Low	0.05	0.4	0.8	0.1	0.2	0.6
SLVS33 ⁶	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.2	0.3
		Low	0.05	0.2	0.8	0.1	0.2	0.3
SLVS25 ⁶	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.2	0.3
		Low	0.05	0.2	0.8	0.1	0.2	0.3
SLVS18 ⁵	HSIO	Mid (default)	0.6	1.00	1.65	0.1	0.2	0.3
		Low	0.05	0.4	0.8	0.1	0.2	0.3
HCSL33 ⁶	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.55	1.1
		Low	0.05	0.35	0.8	0.1	0.55	1.1

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V _{ICM} ^{1,3} Min (V)	V _{ICM} ^{1,3} Typ (V)	V _{ICM} ^{1,3} Max (V)	V _{ID} ² Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
HCSL25 ⁶	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.55	1.1
		Low	0.05	0.35	0.8	0.1	0.55	1.1
HCSL18 ⁵	HSIO	Mid (default)	0.6	1.0	1.65	0.1	0.55	1.1
		Low	0.05	0.4	0.8	0.1	0.55	1.1
BUSLVDSE25	GPIO	Mid (default)	0.6	1.25	2.35	0.05	0.1	V _{DDIn}
		Low	0.05	0.4	0.8	0.05	0.1	V _{DDIn}
MLVDSE25	GPIO	Mid (default)	0.6	1.25	2.35	0.05	0.35	2.4
		Low	0.05	0.4	0.8	0.05	0.35	2.4
LVPECL33	GPIO	Mid (default)	0.6	1.65	2.35	0.05	0.8	2.4
		Low	0.05	0.4	0.8	0.05	0.8	2.4
LVPECL33	GPIO	Mid (default)	0.6	1.65	2.35	0.05	0.8	2.4
		Low	0.05	0.4	0.8	0.05	0.8	2.4
MIPI25	GPIO	Mid (default)	0.6	1.25	2.35	0.05	0.2	0.3
		Low	0.05	0.2	0.8	0.05	0.2	0.3

1. V_{ICM} is the input common mode.
2. V_{ID} is the input differential voltage.
3. V_{ICM} rules are as follows:
 - a. V_{ICM} must be less than V_{DDI} – 0.4 V;
 - b. V_{ICM} + V_{ID}/2 must be <V_{DDI} + 0.4 V;
 - c. V_{ICM} – V_{ID}/2 must be >V_{SS} – 0.3 V;
 - d. Any differential input with V_{ICM} ≤ 0.6 V requires the low common mode setting in Libero (VICM_RANGE=LOW).
4. V_{DDI} = 1.8 V, V_{DDAUX} = 2.5 V.
5. HSIO receiver only.
6. GPIO receiver only.

Table 15 • Differential DC Output Levels

I/O Standard	Bank Type	V _{OCM} ¹ Min (V)	V _{OCM} Typ (V)	V _{OCM} Max (V)	V _{OD} ² Min (V)	V _{OD} ² Typ (V)	V _{OD} ² Max (V)
LVDS33	GPIO		1.2		0.25	0.35	0.45
LVDS25	GPIO		1.2		0.25	0.35	0.45
LCMDS33	GPIO		0.6		0.25	0.35	0.45
LCMDS25	GPIO		0.6		0.25	0.35	0.45
RSDS33	GPIO		1.2		0.17	0.2	0.23
RSDS25	GPIO		1.2		0.17	0.2	0.23
MINILVDS33	GPIO		1.2		0.3	0.4	0.6
MINILVDS25	GPIO		1.2		0.3	0.4	0.6
SUBLVDS33	GPIO		0.9		0.1	0.15	0.3
SUBLVDS25	GPIO		0.9		0.1	0.15	0.3
PPDS33	GPIO		0.8		0.17	0.2	0.23
PPDS25	GPIO		0.8		0.17	0.2	0.23
SLVSE15 ³	GPIO, HSIO		0.2		0.12	0.135	0.15
BUSLVDSE25 ³	GPIO		1.25		0.24	0.262	0.272

Figure 1 • Output Delay Measurement—Single-Ended Test Setup

Figure 2 • Output Delay Measurement—Differential Test Setup


7.1.3 Input Buffer Speed

The following tables provide information about input buffer speed.

Table 24 • HSIO Maximum Input Buffer Speed

Standard	STD	-1	Unit
LVDS18	1250	1250	Mbps
RDS18	800	800	Mbps
MINILVDS18	800	800	Mbps
SUBLVDS18	800	800	Mbps
PPDS18	800	800	Mbps
SLVS18	800	800	Mbps
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps

7.1.5 Maximum PHY Rate for Memory Interface IP

The following tables provide information about the maximum PHY rate for memory interface IP.

Table 28 • Maximum PHY Rate for Memory Interfaces IP for HSIO Banks

Memory Standard	Gearing Ratio	VDDAUX	VDDI	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR4	8:1	1.8 V	1.2 V	1333	1600	167	200
DDR3	8:1	1.8 V	1.5 V	1067	1333	133	167
DDR3L	8:1	1.8 V	1.35 V	1067	1333	133	167
LPDDR3	8:1	1.8 V	1.2 V	1067	1333	133	167
QDRII+	8:1	1.8 V	1.5 V	900	1100	112.5	137.5
RLDRAM3 ¹	8:1	1.8 V	1.35 V	1067	1067	133	133
RLDRAM3 ¹	4:1	1.8 V	1.35 V	667	800	167	200
RLDRAM3 ¹	2:1	1.8 V	1.35 V	333	400	167	200
RLDRAM2 ¹	8:1	1.8 V	1.8 V	800	1067	100	133
RLDRAM2 ¹	4:1	1.8 V	1.8 V	667	800	167	200
RLDRAM2 ¹	2:1	1.8 V	1.8 V	333	400	167	200

1. RLDRAM2 and RLDRAM3 are not supported with a soft IP controller currently.

Table 29 • Maximum PHY Rate for Memory Interfaces IP for GPIO Banks

Memory Standard	Gearing Ratio	VDDAUX	VDDI	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR3	8:1	2.5 V	1.5 V	800	1067	100	133
QDRII+	8:1	2.5 V	1.5 V	900	900	113	113
RLDRAM2 ¹	4:1	2.5 V	1.8 V	800	800	200	200
RLDRAM2 ¹	2:1	2.5 V	1.8 V	400	400	200	200

1. RLDRAM2 is currently not supported with a soft IP controller.

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Clock-to-Data Condition
F _{MAX} 4:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 8:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 2:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 4:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Regional clock duty cycle distortion	T _{DCDR}	120	120	120	120	ps	At 250 MHz

The following table provides clocking specifications from –40 °C to 100 °C.

Table 36 • High-Speed I/O Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
High-speed I/O clock F _{MAX}	F _{MAXB}	1000	1250	1000	1250	MHz	HSIO and GPIO
High-speed I/O clock skew ¹	F _{SKEWB}	30	20	30	20	ps	HSIO without bridging
	F _{SKEWB}	600	500	600	500	ps	HSIO with bridging
	F _{SKEWB}	45	35	45	35	ps	GPIO without bridging
	F _{SKEWB}	75	60	75	60	ps	GPIO with bridging
High-speed I/O clock duty cycle distortion ²	T _{DCB}	90	90	90	90	ps	HSIO without bridging
	T _{DCB}	115	115	115	115	ps	HSIO with bridging
	T _{DCB}	90	90	90	90	ps	GPIO without bridging
	T _{DCB}	115	115	115	115	ps	GPIO with bridging

1. F_{SKEWB} is the worst-case clock-tree skew observable between sequential I/O elements. Clock-tree skew is significantly smaller at I/O registers close to each other and fed by the same or adjacent clock-tree branches. Use the Microsemi Timing Analyzer tool to evaluate clock skew specific to the design.
2. Parameters listed in this table correspond to the worst-case duty cycle distortion observable at the I/O flip flops. IBIS should be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times for any I/O standard.

7.2.2

PLL

The following table provides information about PLL.

Table 37 • PLL Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input clock frequency (integer mode)	F _{INI}	1		1250	MHz
Input clock frequency (fractional mode)	F _{INF}	10		1250	MHz
Minimum reference or feedback pulse width ¹	F _{INPULSE}	200			ps
Frequency at the Frequency Phase Detector (PFD) (integer mode)	F _{PHDET1}	1		312	MHz
Frequency at the PFD (fractional mode)	F _{PHDET2}	10	50	125	MHz
Allowable input duty cycle	F _{INDUTY}	25		75	%

Parameter	Symbol	Min	Typ	Max	Unit
Operating current (V_{DD18})	RC_{SCVPP}			0.1	μA
Operating current (V_{DD})	RC_{SCVDD}			60.7	μA

7.3 Fabric Specifications

The following section describes specifications for the fabric.

7.3.1 Math Blocks

The following tables describe math block performance.

Table 41 • Math Block Performance Extended Commercial Range (0 °C to 100 °C)

Parameter	Symbol	Modes	V _{DD} = 1.0 V – STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V – STD	V _{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	370	470	440	500	MHz
		18 × 18 multiplication summed with 48-bit input	370	470	440	500	MHz
		18 × 19 multiplier pre-adder ROM mode	365	465	435	500	MHz
		Two 9 × 9 multiplication	370	470	440	500	MHz
		9 × 9 dot product (DOTP)	370	470	440	500	MHz
		Complex 18 × 19 multiplication	360	455	430	500	MHz

Table 42 • Math Block Performance Industrial Range (–40 °C to 100 °C)

Parameter	Symbol	Modes	V _{DD} = 1.0 V – STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V – STD	V _{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	365	465	435	500	MHz
		18 × 18 multiplication summed with 48-bit input	365	465	435	500	MHz
		18 × 19 multiplier pre-adder ROM mode	355	460	430	500	MHz
		Two 9 × 9 multiplication	365	465	435	500	MHz
		9 × 9 DOTP	365	465	435	500	MHz
		Complex 18 × 19 multiplication	350	450	425	500	MHz

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Reference clock input rate ^{1, 2, 3}	F _{XCVRREFCLKMAX} CASCADE	20		156	20		156	MHz
Reference clock rate at the PFD ⁴	F _{TXREFCLKPFD}	20		156	20		156	MHz
Reference clock rate recommended at the PFD for Tx rates 10 Gbps and above ⁴	F _{TXREFCLKPFD10G}	75		156	75		156	MHz
Tx reference clock phase noise requirements to meet jitter specifications (156 MHz clock at reference clock input) ⁵	F _{TXREFPN}			–110			–110	dBc /Hz
Phase noise at 10 KHz	F _{TXREFPN}			–110			–110	dBc /Hz
Phase noise at 100 KHz	F _{TXREFPN}			–115			–115	dBc /Hz
Phase noise at 1 MHz	F _{TXREFPN}			–135			–135	dBc /Hz
Reference clock input rise time (10%–90%)	T _{REFRISE}		200	500		200	500	ps
Reference clock input fall time (90%–10%)	T _{REFFALL}		200	500		200	500	ps
Reference clock duty cycle	T _{REFDUTY}	40		60	40		60	%
Spread spectrum modulation spread ⁶	Mod_Spread	0.1		3.1	0.1		3.1	%
Spread spectrum modulation frequency ⁷	Mod_Freq	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	KHz

1. See the maximum reference clock rate allowed per input buffer standard.
2. The minimum value applies to this clock when used as an XCVR reference clock. It does not apply when used as a non-XCVR input buffer (DC input allowed).
3. Cascaded reference clock.
4. After reference clock input divider.
5. Required maximum phase noise is scaled based on actual F_{TxRefClkPFD} value by $20 \times \log_{10} (\text{TxRefClkPFD} / 156 \text{ MHz})$. It is assumed that the reference clock divider of 4 is used for these calculations to always meet the maximum PFD frequency specification.
6. Programmable capability for depth of down-spread or center-spread modulation.
7. Programmable modulation rate based on the modulation divider setting (1 to 63).

7.4.3 Transceiver Reference Clock I/O Standards

The following table describes the differential I/O standards supported as transceiver reference clocks.

Table 52 • PolarFire Transceiver Transmitter Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Differential termination	V_{TERM}		85		Ω	
	V_{TERM}		100		Ω	
	V_{TERM}		150		Ω	
Common mode voltage ¹	V_{OCM}	$0.44 \times V_{\text{DDA}}$	$0.525 \times V_{\text{DDA}}$	$0.59 \times V_{\text{DDA}}$	V	DC coupled 50% setting
	V_{OCM}	$0.52 \times V_{\text{DDA}}$	$0.6 \times V_{\text{DDA}}$	$0.66 \times V_{\text{DDA}}$	V	DC coupled 60% setting
	V_{OCM}	$0.61 \times V_{\text{DDA}}$	$0.7 \times V_{\text{DDA}}$	$0.75 \times V_{\text{DDA}}$	V	DC coupled 70% setting
	V_{OCM}	$0.63 \times V_{\text{DDA}}$	$0.8 \times V_{\text{DDA}}$	$0.83 \times V_{\text{DDA}}$	V	DC coupled 80% setting
Rise time ²	T_{TXRF}	41		70	ps	20% to 80%
Fall time ²		41		70	ps	80% to 20%
Differential peak-to-peak amplitude	V_{ODPP}		1040		mV	1000 mV setting
	V_{ODPP}		840		mV	800 mV setting
	V_{ODPP}		630		mV	600 mV setting
	V_{ODPP}		620		mV	500 mV setting
	V_{ODPP}		530		mV	400 mV setting
	V_{ODPP}		360		mV	300 mV setting
	V_{ODPP}		240		mV	200 mV setting
	V_{ODPP}		160		mV	100 mV setting
Transmit lane P to N skew ³	T_{OSKEW}		8	15	ps	
Lane to lane transmit skew ⁴	T_{LLSKEW}			75	ps	Single PLL
					ps	Multiple PLL
Electrical idle transition entry time ⁷	$T_{\text{TxElTrEntry}}$				ns	
Electrical idle transition exit time ⁷	$T_{\text{TxElTrExit}}$				ns	
Electrical idle amplitude	V_{TxElpp}				mV	
TXPLL lock time	T_{TXLock}			1600	PFD cycles	
Digital PLL lock time ⁸	T_{DPLLlock}				REFCLK UIs	
Total jitter ^{5,6}	T_{J}				UI	Data rate ≥ 8.5 Gbps to 12.7 Gbps ⁹
Deterministic jitter ^{5,6}	T_{DJ}				UI	(Tx V_{CO} rate 4.25 GHz to 6.35 GHz)
Total jitter ^{5,6}	T_{J}			0.28	UI	Data rate ≥ 3.2 Gbps to 8.5 Gbps
Deterministic jitter ^{5,6}	T_{DJ}			0.07	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)
Total jitter ^{5,6}	T_{J}			0.28	UI	Data rate ≥ 1.6 Gbps to 3.2 Gbps
Deterministic jitter ^{5,6}	T_{DJ}			0.07	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)
Total jitter ^{5,6}	T_{J}			0.13	UI	Data rate ≥ 800 Mbps to 1.6 Gbps
Deterministic jitter ^{5,6}	T_{DJ}			0.02	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)
Total jitter ^{5,6}	T_{J}			0.06	UI	Data rate = 250 Mbps to 800 Mbps
Deterministic jitter ^{5,6}	T_{DJ}			0.01	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)

1. Increased DC common mode settings above 50% reduce allowed V_{OD} output swing capabilities.
2. Adjustable through transmit emphasis.
3. With estimated package differences.
4. Single PLL applies to all four lanes in the same quad location with the same TxPLL.

Table 55 • PCI Express Gen2

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps		0.35	UI
Receiver jitter tolerance	5.0 Gbps	0.4		UI

Note: With add-in card as specified in PCI Express CEM Rev 2.0.

7.5.2 Interlaken

The following table describes Interlaken.

Table 56 • Interlaken

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	6.375 Gbps		0.3	UI
	10.3125 Gbps		0.3	UI
	12.7 Gbps ¹			UI
Receiver jitter tolerance	6.375 Gbps	0.6		UI
	10.3125 Gbps	0.65		UI
	12.7 Gbps ¹			UI

- For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions](#) (see page 6).

7.5.3 10GbE (10GBASE-R, and 10GBASE-KR)

The following table describes 10GbE (10GBASE-R).

Table 57 • 10GbE (10GBASE-R)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps		0.28	UI
Receiver jitter tolerance	10.3125 Gbps	0.7		UI

The following table describes 10GbE (10GBASE-KR).

Table 58 • 10GbE (10GBASE-KR)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps			UI
Receiver jitter tolerance	10.3125 Gbps			UI

The following table describes 10GbE (XAUI).

Table 59 • 10GbE (XAUI)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter (near end)	3.125 Gbps		0.35	UI
Total transmit jitter (far end)			0.55	UI
Receiver jitter tolerance	3.125 Gbps	0.65		UI

The following table describes 10GbE (RXAUI).

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data PNVM data (non-recoverable) ^{1, 4}			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 79 • Zeroization Times for MPF300T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1, 4}			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 80 • Zeroization Times for MPF500T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	One iteration of scrubbing

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ¹			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

7.6.7 Verify Time

The following tables describe verify time.

Table 81 • Standalone Fabric Verify Times

Parameter	Devices	Max	Unit
Standalone verification over JTAG	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	53 ¹	s
	MPF300T, TL, TS, TLS	90 ¹	s
	MPF500T, TL, TS, TLS		s
Standalone verification over SPI	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	37 ²	s
	MPF300T, TL, TS, TLS	55 ²	s
	MPF500T, TL, TS, TLS		s

1. Programmer: FlashPro5, TCK 10 MHz; PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.
2. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. DirectC version 4.1.

Notes:

- Standalone verify is limited to 2,000 total device hours over the industrial –40 °C to 100 °C temperature.
- Use the digest system service, for verify device time more than 2,000 hours.
- Standalone verify checks the programming margin on both the P and N gates of the push-pull cell.
- Digest checks only the P side of the push-pull gate. However, the push-pull gates work in tandem. Digest check is recommended if users believe they will exceed the 2,000-hour verify time specification.

Table 82 • Verify Time by Programming Hardware

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF100T, TL, TS, TLS						
MPF200T, TL, TS, TLS	9	67	53			s
MPF300T, TL, TS, TLS	14	95	90			s

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Secure NVM read	T _{SNVM_Rd}	18H				Note 1
Digital signature service raw	T _{SIG_RAW}	19H	174	187	ms	
Digital signature service DER	T _{SIG_DER}	1AH	174	187	ms	
Reserved		1BH–1FH				
PUF emulation	T _{Challenge}	20H	1.8	2.0	ms	
Nonce service	T _{Nonce}	21H	1.2	1.4	ms	
Bitstream authentication	T _{BIT_AUTH}	22H				Note 4
IAP Image authentication	T _{IAP_AUTH}	23H				Note 4
Reserved		26H–3FH				
In application programming by index	T _{IAP_Prg_Index}	42H				Note 2
In application programming by SPI address	T _{IAP_Prg_Addr}	43H				Note 2
In application verify by index	T _{IAP_Ver_Index}	44H				Note 5
In application verify by SPI address	T _{IAP_Ver_Addr}	45H				Note 5
Auto update	T _{AutoUpdate}	46H				Note 2
Digest check	T _{digest_chk}	47H				Note 3

1. See [sNVM Read/Write Characteristics](#) (see page 58).
2. See [SPI Master Programming Time](#) (see page 52).
3. See [Digest Times](#) (see page 54).
4. See [Authentication Services Time](#) (see page 58).
5. See [Verify Services Time](#) (see page 58).
6. Throughputs described are measured from SS_REQ assertion to BUSY de-assertion.

7.8 Fabric Macros

This section describes switching characteristics of UJTAG, UJTAG_SEC, USPI, system controller, and temper detectors and dynamic reconfiguration details.

7.8.1 UJTAG Switching Characteristics

The following section describes characteristics of UJTAG switching.

Table 88 • UJTAG Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F _{TCK}			25	MHz	

1. With DPA counter measures.

Table 115 • HMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
HMAC-SHA-256 ¹ , 256-bit key	512	7477	2361
	64K	88367	2099
HMAC-SHA-384 ¹ , 384-bit key	1024	13049	2257
	64K	106103	2153

1. With DPA counter measures.

Table 116 • CMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-CMAC-256 ¹ (message is only authenticated)	128	446	9058
	64K	45494	111053

1. With DPA counter measures.

Table 117 • KEY TREE

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
128-bit nonce + 8-bit optype		102457	2751
256-bit nonce + 8-bit optype		103218	2089

Table 118 • SHA

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
SHA-1 ¹	512	2386	1579
	64K	77576	990
SHA-256 ¹	512	2516	884
	64K	84752	938
SHA-384 ¹	1024	4154	884
	64K	100222	938
SHA-512 ¹	1024	4154	881
	64K	100222	935

1. With DPA counter measures.

Table 119 • ECC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
ECDSA SigGen, P-384/SHA-384 ¹	1024	12528912	6944
	8K	12540448	5643
ECDSA SigGen, P-384/SHA-384	1024	5502928	6155

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